

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **MRF314** is Designed for Class C Power Amplifier Applications up to 200 MHz.

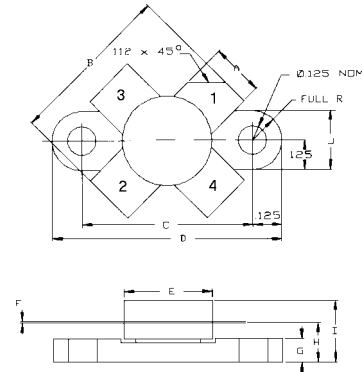
FEATURES:

- $P_G = 10$ dB min. at 30 W/ 150 MHz
- Withstands **30:1** Load VSWR
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	3.4 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	82 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	2.13 $^\circ C/W$

PACKAGE STYLE .380 4L FLG



	MINIMUM (1st 100000)	MAXIMUM (1st 100000)
A	200/15.0	200/15.0
B	200/15.0	200/15.0
C	175/13.0	175/13.0
D	175/13.0	175/13.0
E	175/13.0	175/13.0
F	175/13.0	175/13.0
G	175/13.0	175/13.0
H	175/13.0	175/13.0
I	175/13.0	175/13.0
J	175/13.0	175/13.0

ORDER CODE: ASI10872

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 30$ mA	35			V
BV_{CES}	$I_C = 30$ mA	65			V
BV_{EBO}	$I_E = 3.0$ mA	4.0			V
I_{CBO}	$V_E = 30$ V			3.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.5$ A	20		80	---
C_{OB}	$V_{CB} = 30$ V $f = 1.0$ MHz		30	40	pF
P_G	$V_{CC} = 28$ V $P_{OUT} = 30$ W $f = 150$ MHz	10	13.5		dB
η_c		50			%
ψ		30:1 all phase angles, no degradation in output.			